

Masaya Hamada

List of Publications by Year in descending order

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#	ARTICLE	IF	CITATIONS
1	High Hall-Effect Mobility of Large-Area Atomic-Layered Polycrystalline ZrS ₂ Film Using UHV RF Magnetron Sputtering and Sulfurization. IEEE Journal of the Electron Devices Society, 2019, 7, 1258-1263.	1.2	17
2	Sheet Resistance Reduction of MoS ₂ Film Using Sputtering and Chlorine Plasma Treatment Followed by Sulfur Vapor Annealing. IEEE Journal of the Electron Devices Society, 2021, 9, 278-285.	1.2	10
3	ZrS ₂ symmetrical-ambipolar FETs with near-midgap TiN film for both top-gate electrode and Schottky-barrier contact. Japanese Journal of Applied Physics, 2021, 60, SBBH05.	0.8	8
4	Importance of crystallinity improvement in MoS ₂ film by compound sputtering even followed by post sulfurization. Japanese Journal of Applied Physics, 2021, 60, SBBH10.	0.8	7
5	Hall-effect mobility enhancement of sputtered MoS ₂ film by sulfurization even through Al ₂ O ₃ passivation film simultaneously preventing oxidation. Japanese Journal of Applied Physics, 2020, 59, 105501.	0.8	7
6	Normally-off sputtered-MoS ₂ nMISFETs with TiN top-gate electrode all defined by optical lithography for chip-level integration. Japanese Journal of Applied Physics, 2020, 59, 080906.	0.8	6
7	Elucidation of PVD MoS ₂ film formation process and its structure focusing on sub-monolayer region. Japanese Journal of Applied Physics, 2022, 61, SC1023.	0.8	5
8	WS ₂ Film by Sputtering and Sulfur-Vapor Annealing, and its pMISFET with TiN/HfO ₂ Top-Gate Stack, TiN Bottom Contact, and Ultra-Thin Body and Box. IEEE Journal of the Electron Devices Society, 2021, , 1-1.	1.2	3
9	High Seebeck coefficient in PVD-WS ₂ film with grain size enlargement. Japanese Journal of Applied Physics, 0, , .	0.8	3
10	Positive Seebeck coefficient of niobium-doped MoS ₂ film deposited by sputtering and activated by sulfur vapor annealing. Japanese Journal of Applied Physics, 2022, 61, 075506.	0.8	1
11	Self-aligned-TiSi ₂ bottom contact with APM cleaning and post-annealing for sputtered-MoS ₂ film. Japanese Journal of Applied Physics, 2021, 60, SBBH04.	0.8	0
12	Side-Contact Architecture for p/n-Stacked-Nano-Sheet ZrS ₂ 2D-FETs Beyond 1-nm Technology Node. , 2021, , .		0